Silicon NPN Power Transistors BUW35

DESCRIPTION

·With TO-3 package
·High breakdown voltage

APPLICATIONS

·For high voltage ,fast switching applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	800	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		10	A
I_{CM}	Collector current-peak		15	A
I_B	Base current		5	A
P_T	Total power dissipation	T_C≤25□	125	W
T_j	Junction temperature		200	□
T_{stg}	Storage temperature		-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}c}$	Thermal resistance from junction to case	1.4	□/W

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA ; I_B=0	400			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=8A; I_B=2.5A			1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=8A; I_B=2.5A			1.8	V
I_{CES}	Collector cut-off current	V_{CE}=800V ;V_{BE}=0 T_C=125□			0.1 3.0	mA
I_{EBO}	Emitter cut-off current	V_{EB}=7V; I_C=0			1	mA
h_{FE-1}	DC current gain	I_C=1A ; V_{CE}=5V	15		50	
h_{FE-2}	DC current gain	I_C=5A ; V_{CE}=5V	8			

Switching times

t_{on}	Turn-on time	I_C=5A ;I_{B1}=- I_{B2}=1A V_{CC}=250V			0.7	μs
t_s	Storage time				3.0	μs
t_f	Fall time				0.8	μs

PACKAGE OUTLINE

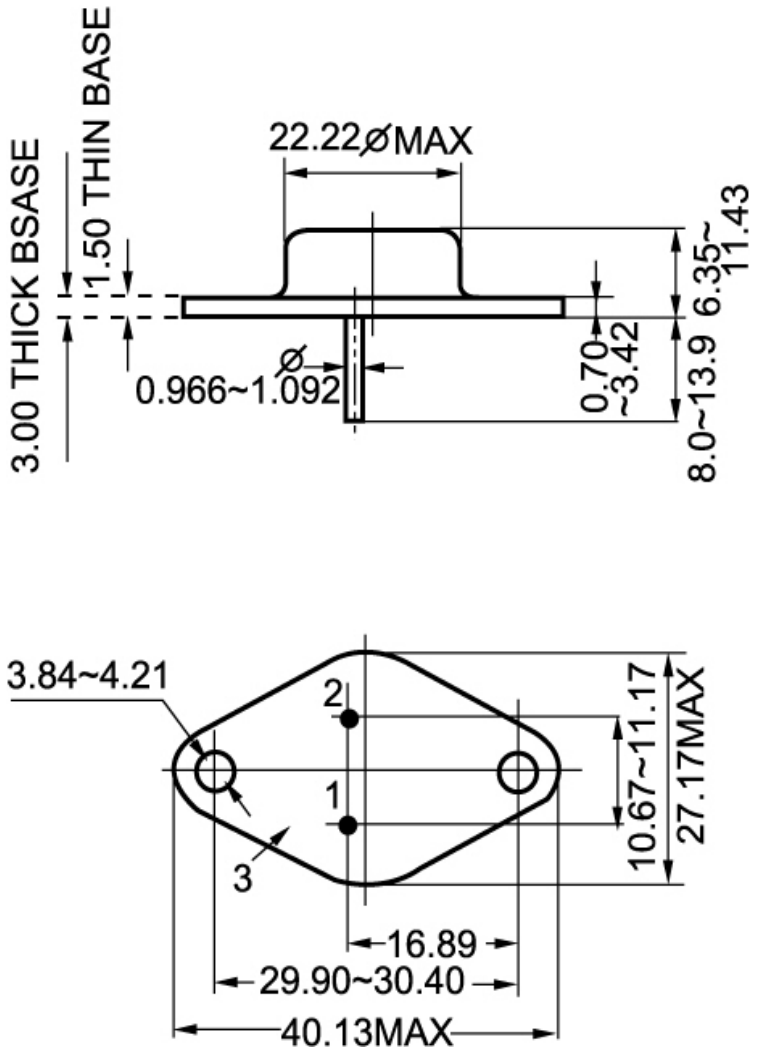

Fig.2 Outline dimensions